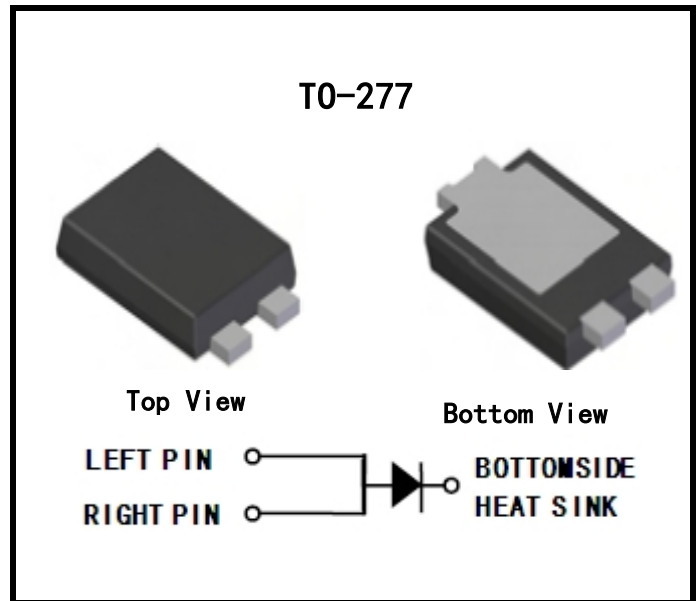


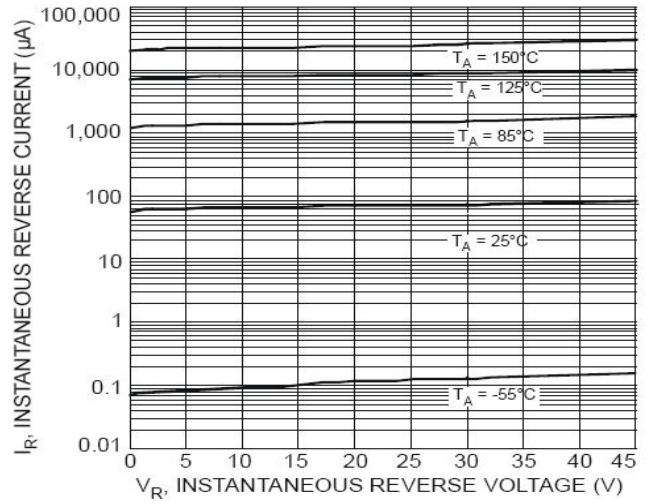
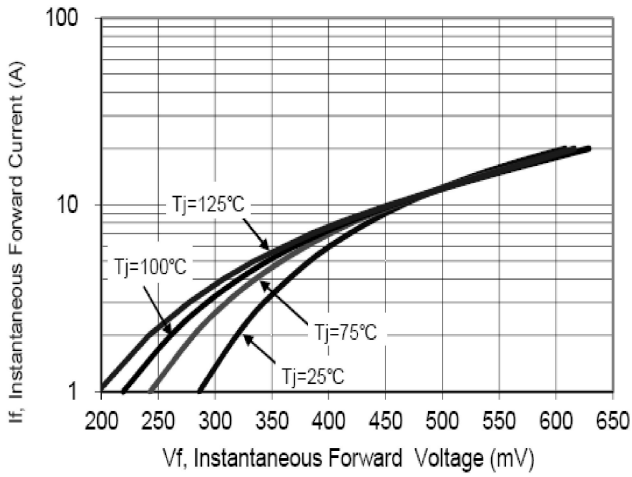
Ultra Low VF=0.35V at IF=2A
FEATURES

- * Schottky Barrier Chip
- * Guard Ring Die Construction for Transient Protection
- * Low Power Loss, High Efficiency
- * High Surge Capability
- * High Current Capability and Low Forward Voltage Drop
- * For Use in Low Voltage, High Frequency Inverters, Free Wheeling, and Polarity Protection Applications

PACKAGE

ELECTRICAL CHARACTERISTICS (Tamb=25°C)

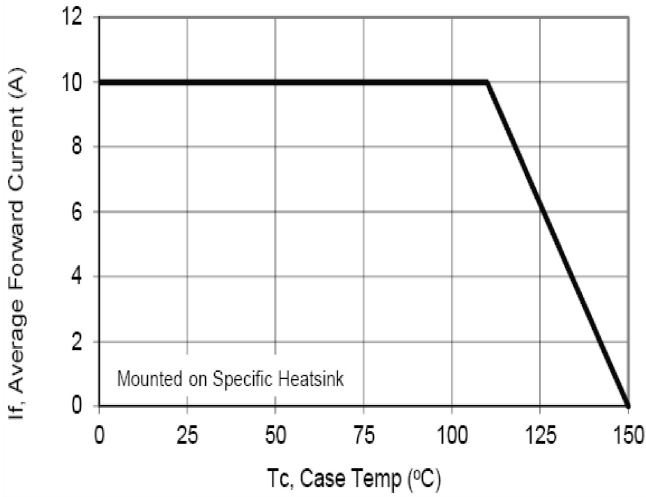
Characteristic	Symbol	Value		Unit
Peak Repetitive Reverse Voltage	V_{RRM}	45		V
DC Blocking Voltage	V_R	45		
Average Rectified Output Current	$I_{F(AV)}$	10		A
Peak Forward Surge Current 8.3ms single half sine-wave superimposed on rated load (JEDEC method)	I_{FSM}	280		A
Maximum Instantaneous Forward Voltage @IF=2A, TC=25°C @IF=2A, TC=125°C @IF=5A, TC=25°C @IF=5A, TC=125°C @IF=10A, TC=25°C @IF=10A, TC=125°C	V_F	TYP.	MAX.	V
		0.35	0.4	
		0.29	0.35	
		0.41	0.45	
		0.33	0.39	
		0.46	0.5	
Peak Reverse Current @TA=25 °C	I_R	0.3		mA
at Rated DC Blocking Voltage @TA=125°C		20		
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150		°C
Typical Junction Capacitance	C_J	600		pF
Maximum Thermal Resistance	θ_{JA}	31		°C/W
	θ_{JM}	4		

Characteristics Curves



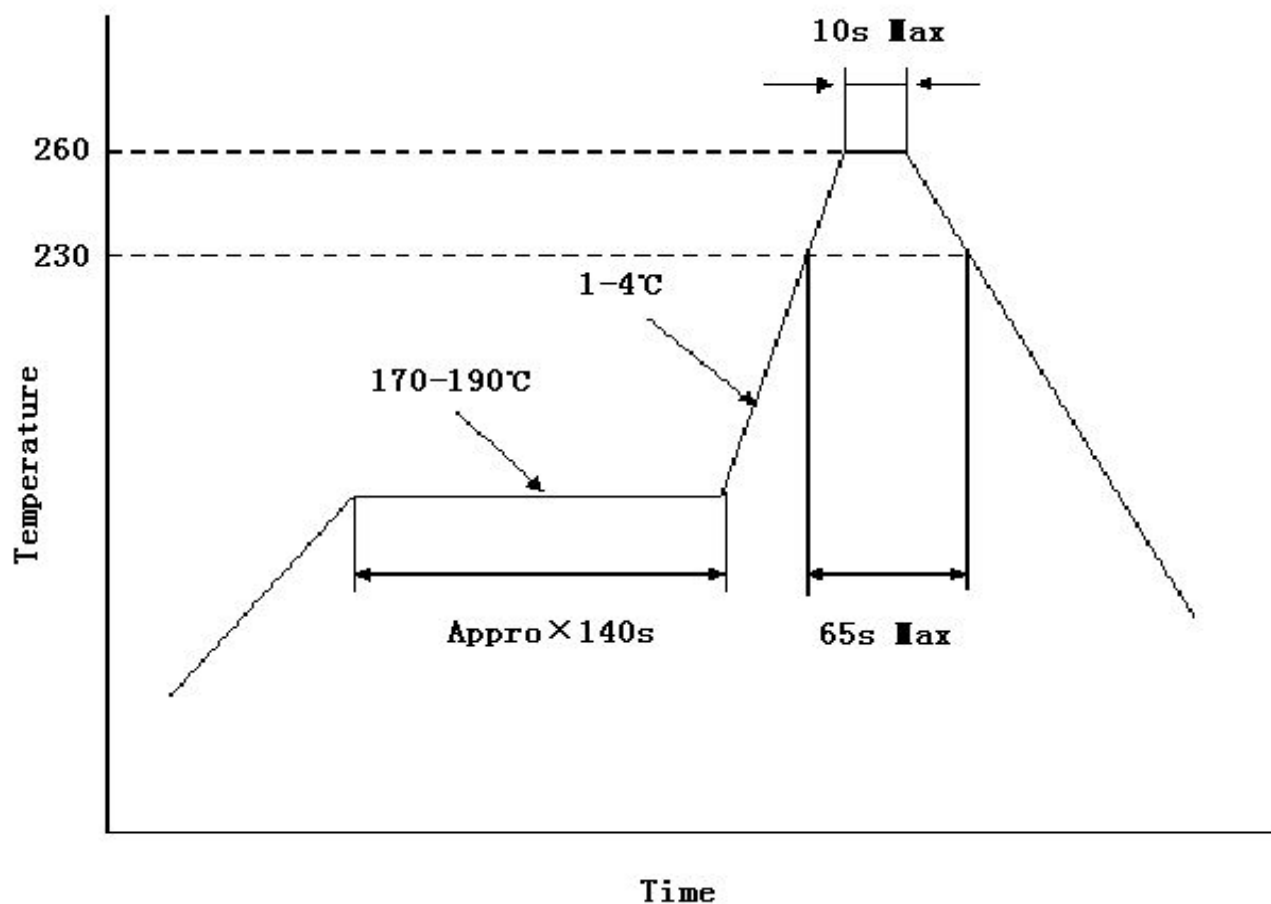
Typical Forward Voltage Per Diode

Typical Reverse Current Per Diode



Average Forward Current vs. Case Temperature Per Diode

■ Reflow Soldering Temperature Profile



TO-277 MECHANICAL DATA

UNIT: mm

SYMBOL	MIN	MAX	SYMBOL	MIN	MAX
A	1.05	1.2	e	1.65	1.95
A2	0.3	0.45	E	6.3	6.6
b1	0.8	1	E1	5.3	5.8
b2	1.7	1.9	E2	3.1	3.6
b3	0.7	0.9	L	0.5	0.7
D	3.85	4.3	L1	0.5	0.7
D2	2.9	3.3	L2	0.8	1.1
W	1.1	1.4	h	0.1	0.2
W1	0.3	0.5			

